TITLE

by

Kraig Andrews

Ph.D. Disseration Prospectus

YEAR		
Advisor		
Advisor		

${\bf ABSTRACT}$

TITLE HERE

by

Kraig J. Andrews

August 2008

Advisor: Dr. Zhixain Zhou

Major: Physics

Degree: Doctor of Philosophy

Abstract here

ACKNOWLEDGEMENTS

 ${\bf Acknowledgements\ here...}$

Table of Contents

	List of Figures	1V
	List of Tables	V
1	Introduction	1
	1.1 The Conception of Semiconductors	1
	1.2 Evolution of Semiconductors	2
	 1.2 Evolution of Semiconductors 1.3 Interest and Development of Two-dimensional Materials 1.5 Evolution of Semiconductors 1.6 Evolution of Semiconductors 1.7 Evolution of Semiconductors 1.8 Evolution of Semiconductors 1.9 Evolution of Semiconductors 1.1 Evolution of Semiconductors 1.2 Evolution of Semiconductors 1.3 Interest and Development of Two-dimensional Materials 1.4 Evolution of Semiconductors 1.5 Evolution of Semiconductors 1.6 Evolution of Semiconductors 1.7 Evolution of Semiconductors 1.8 Evolution of Semiconductors 1.8 Evolution of Semiconductors 1.9 Evolution of Semiconductors 1.1 Evolution of Semiconductors 1.2 Evolution of Semiconductors 1.2 Evolution of Semiconductors 1.3 Evolution of Semiconductors 1.4 Evolution of Semiconductors 1.5 Evolution of Semiconductors 1.7 Evolution of	2
	1.4 Current State of Two-dimensional Materials	2
2	Chapter 2	3
	2.1 Section Heading	3
3	Chapter 3	4
	3.1 Section Heading	4
4	Conclusion	5
	Conclusion 4.1 Heading	5
A	Appendices	7

List of Figures

1.1	Name	1
1.2	name	1
1.3	main caption	2

List of Tables

1.1	Properties of selected	semiconductors.																							
-----	------------------------	-----------------	--	--	--	--	--	--	--	--	--	--	--	--	--	--	--	--	--	--	--	--	--	--	--

Introduction

1.1 The Conception of Semiconductors

Here we present work by [2, 1].

Semiconductor	Band Gap (eV)	Electron Mobility ¹ $(cm^2/V \cdot s)$	Hole Mobility ¹ $(cm^2/V \cdot s)$	Lattice Constant (Å)
Si	1.12	1,500	470	5.43095^{a}
Ge	0.67	3,900	1,900	$5.64613^{\rm a}$
GaAs	1.42	8,500	400	$5.6533^{ m b}$
CdS	2.5	300	50	5.8320^{c}
AlAs	2.16	1,200	400	$5.6622^{ m b}$
ZnS	3.66	165	5	$5.410^{\rm d}$

Table 1.1: Selected properties of some common semiconductors at $T = 300 \,\mathrm{K}$. Adapted from ref. [5].

^d Notes on ZnS structure.

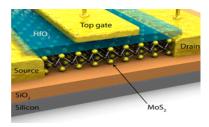


Figure 1.1: Name

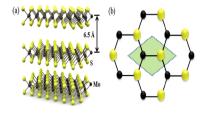


Figure 1.2: name

¹ Drift mobilities in the purest materials.

^a Diamond cubic crystal structure [4].

^b Zinc blende crystal structure [3].

^c Hexagonal and cubic... citation needed.

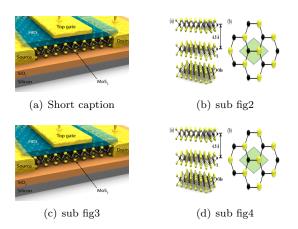


Figure 1.3: main caption

- 1.2 Evolution of Semiconductors
- 1.3 Interest and Development of Two-dimensional Materials
- 1.4 Current State of Two-dimensional Materials

Chapter 2

2.1 Section Heading

Chapter 3

3.1 Section Heading

Conclusion

4.1 Heading

Bibliography

- [1] J. W. Allen. Gallium Arsenide as a Semi-insulator. Nature, 187:403–405, jul 1960.
- [2] M. Cutler and N. F. Mott. Observation of Anderson Localization in an Electron Gas. *Physical Review*, 181:1336–1340, may 1969.
- [3] A. Ledwith and S. J. Moss. *Chemistry of the Semiconductor Industry*. Springer Science, New York, NY, 1 edition, 1989.
- [4] W.C. O'Mara, R.B. Herring, and L.P. Hunt. *Handbook of Semiconductor Silicon Technology*. Materials science and process technology series. Noyes Publications, 1990.
- [5] Dieter K. Schroder. Semiconductor Material and Device Characterization. John Wiley and Sons, Inc., Hoboken, New Jersey, 3rd edition, 2006.

Appendices

Text goes here...